

Self-Powered Single-Channel Isolated GaNFET Driver with Power-Thru Integrated Isolated Bias Supply

FEATURES AND BENEFITS

- Power-Thru integrated isolated bias
 - No high-side bootstrap
 - No external secondary-side bias
- 50 ns propagation delay, with excellent device-to-device matching of 5 ns
- Separate drive output pins: pull-up (2.8Ω) and pull-down (1.0Ω)
- Supply voltage $10.5 \text{ V} < V_{\text{DRV}} < 13.2 \text{ V}$
- Undervoltage lockout on primary V_{DRV} and secondary V_{SEC}
- Enable pin with fast response
- Continuous ON capability—no need to recycle IN or recharge bootstrap capacitor
- CMTI $> 100 \text{ V/ns}$ dv/dt immunity
- Creepage distance $> 8 \text{ mm}$
- Distance-through-insulation DTI $\geq 450 \mu\text{m}$
- Safety Regulatory Approvals (pending)
 - 5.7 kV RMS V_{ISO} per UL 1577
 - 8 kV pk V_{IOTM} maximum transient isolation voltage per VDE0884-11
 - 630 V pk maximum working isolation voltage

APPLICATIONS

- **AC-DC and DC-DC converters:** Totem-pole PFC, LLC half-/full-bridge, SR drive, multi-level converters, phase-shifted full-bridge
- **Automotive:** EV chargers, motor drives
- **Industrial:** transportation, robotics
- **Grid Infrastructure:** micro-inverters, solar

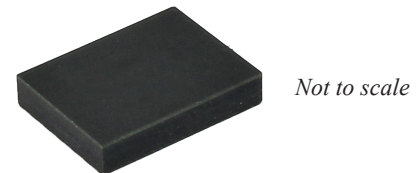
DESCRIPTION

The AHV85110 isolated gate driver is optimized for driving GaNFETs in multiple applications and topologies. An isolated output bias supply is integrated into the driver device, eliminating the need for any external gate drive auxiliary bias supply or high-side bootstrap. This greatly simplifies the system design and reduces EMI through reduced total common-mode (CM) capacitance. It also allows the driving of a floating switch in any location in a switching power topology.

The driver has fast propagation delay and high peak source/sink capability to efficiently drive GaNFETs in high-frequency designs. High CMTI combined with isolated outputs for both bias power and drive make it ideal in applications requiring isolation, level-shifting, or ground separation for noise immunity.

The device is available in a compact low-profile surface-mount NH package. Several protection features are integrated, including undervoltage lockout on primary and secondary bias rails, internal pull-down on IN pin and OUTPD pin, fast response enable input, and OUT pulse synchronization with first IN rising edge after enable (avoids asynchronous runt pulses).

PACKAGE



10 mm × 7.66 mm × 2.53 mm
12-pin low-profile surface mount

TYPICAL APPLICATION

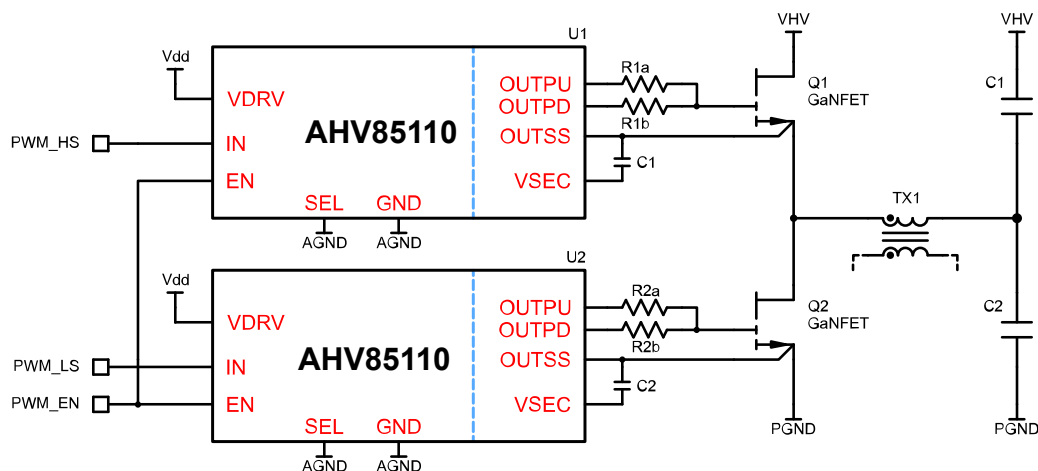


Figure 1: Typical AHV85110 half-bridge application—eliminates high-side bootstrap

AHV85110

Self-Powered Single-Channel Isolated GaNFET Driver with Power-Thru Integrated Isolated Bias Supply

SELECTION GUIDE

Part Number	Switch	# of Channels	Output	Isolation	Package
AHV85110KNHTR	GaN Driver	1	Unipolar	Isolated	10 mm × 7.66 mm × 2.53 mm 12-pin low-profile surface mount

ABSOLUTE MAXIMUM RATINGS [1]

Characteristic	Symbol	Notes	Rating	Unit
Drive Supply Voltage	V_{DRV}	VDRV, wrt to GND	$V_{GND} - 0.5$ to 15	V
Input Data	V_{IN}	IN, wrt to GND	$V_{GND} - 0.5$ to 15	V
Enable	V_{EN}	EN, wrt to GND	$V_{GND} - 0.5$ to 15	V
Select	V_{SEL}	SEL to GND; internal use only	$V_{GND} - 0.5$ to 15	V
Output Drive Pull-Up	V_{OUTPU}	OUTPU to OUTSS	$V_{OUTSS} - 0.5$ to 15	V
Output Drive Pull-Down	V_{OUTPD}	OUTPU to OUTSS	$V_{OUTSS} - 0.5$ to 15	V
Isolated Bias Supply	V_{SEC}	VSEC to OUTSS	$V_{OUTSS} - 0.5$ to 15	V
Junction Temperature	T_J		-40 to 150	°C

[1] Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

VSEC PIN CAPACITOR

Characteristic	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
VSEC Pin Capacitor CSEC	C_{SEC}	External capacitance connected between VSEC and OUTSS pins; external $C_{OUT} = 1$ nF	5 [1]	27	100 [1]	nF

[1] Smaller C_{SEC} values than the recommended typical value can give higher voltage ripple on CSEC.

[2] Larger C_{SEC} values will mean longer startup times.

ESD RATINGS

Characteristic	Symbol	Test Conditions	Value	Unit
Human Body Model	V_{HBM}		±7	kV
Charged Device Model	V_{CDM}		±500	V

THERMAL CHARACTERISTICS: May require derating at maximum conditions; see application information

Characteristic	Symbol	Test Conditions [1]	Value	Unit
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$		TBD	°C/W
Junction-to-Case Thermal Resistance	$R_{\theta JC}$		TBD	°C/W

[1] Additional thermal information available on the Allegro website.

Revision History

Number	Date	Description
–	August 30, 2022	Initial release

Copyright 2022, Allegro MicroSystems.

Allegro MicroSystems reserves the right to make, from time to time, such departures from the detail specifications as may be required to permit improvements in the performance, reliability, or manufacturability of its products. Before placing an order, the user is cautioned to verify that the information being relied upon is current.

Allegro's products are not to be used in any devices or systems, including but not limited to life support devices or systems, in which a failure of Allegro's product can reasonably be expected to cause bodily harm.

The information included herein is believed to be accurate and reliable. However, Allegro MicroSystems assumes no responsibility for its use; nor for any infringement of patents or other rights of third parties which may result from its use.

Copies of this document are considered uncontrolled documents.

For the latest version of this document, visit our website:

www.allegromicro.com